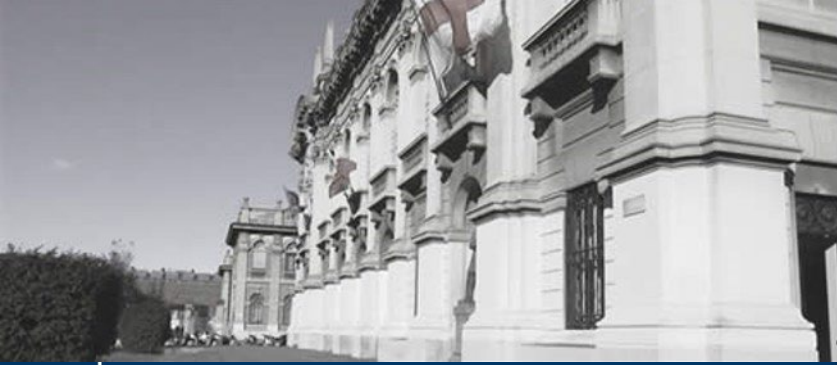




Electronics – 96032

 POLITECNICO DI MILANO



OpAmps Offset Voltage and Bias Currents

Alessandro Spinelli

Phone: (02 2399) 4001

alessandro.spinelli@polimi.it

spinelli.faculty.polimi.it

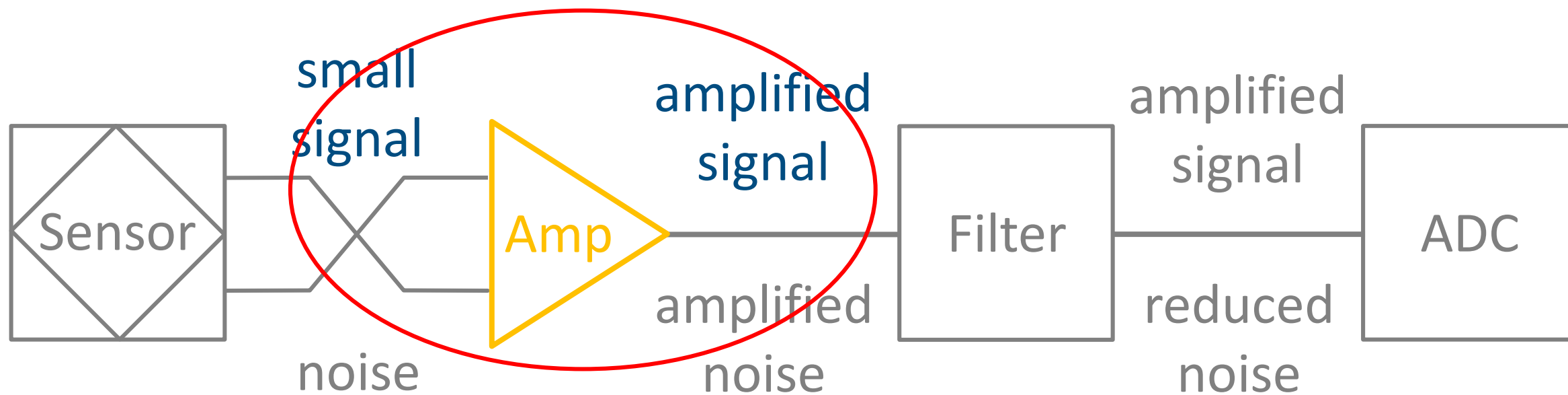


Slides are supplementary material and are NOT a replacement for textbooks and/or lecture notes



Acquisition chain

3



next lessons



Purpose of the lesson

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- We begin our study with the analysis and design of simple amplifiers
- Next lessons will deal with
 - Basic amplifier principles and the feedback amplifier concept
 - Linear applications of OpAmps (this lesson)
 - Feedback amplifier properties
 - Stability of feedback amplifiers
 - Instrumentation amplifiers and OpAmp parameters



- Offset voltage
- Bias currents
- Effect on linear circuits

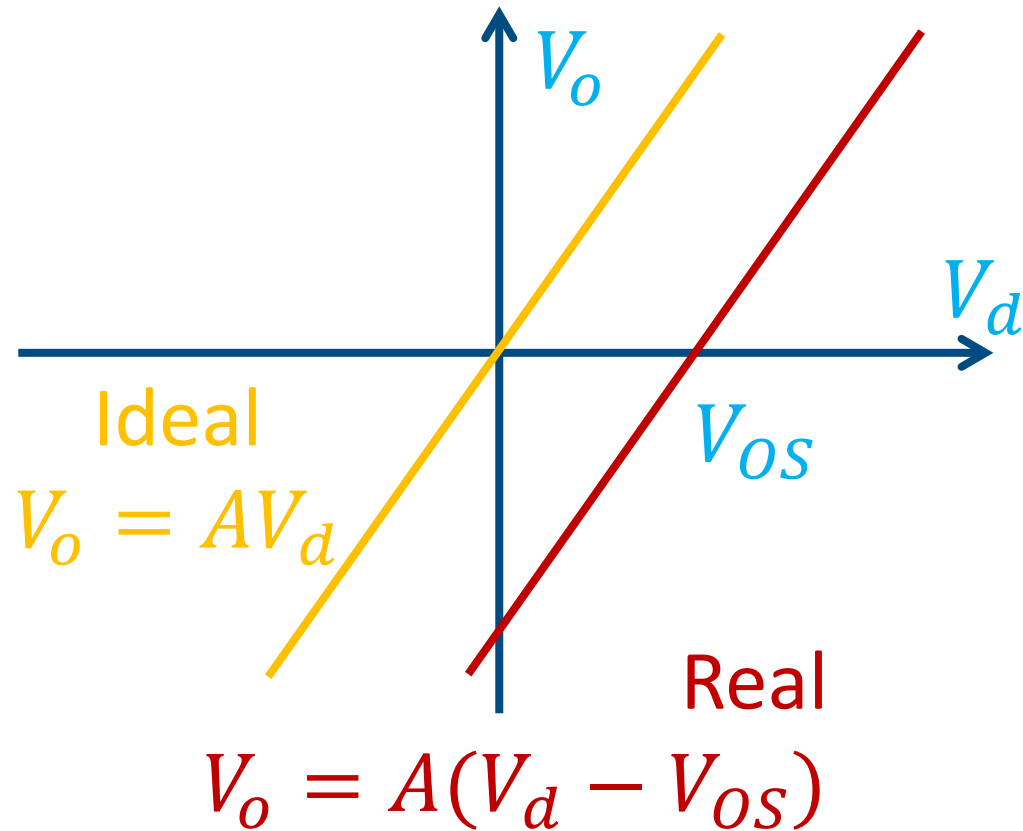


- We begin to remove the OA ideality assumption and discuss the impact on circuits
- OA properties are described by appropriate parameters detailed in manufacturers' datasheets
- There are many OA to choose from
 - Different technology (BJT, JFET, CMOS)
 - Different types (precision, low-drift, rail-to-rail,...)



Input offset voltage

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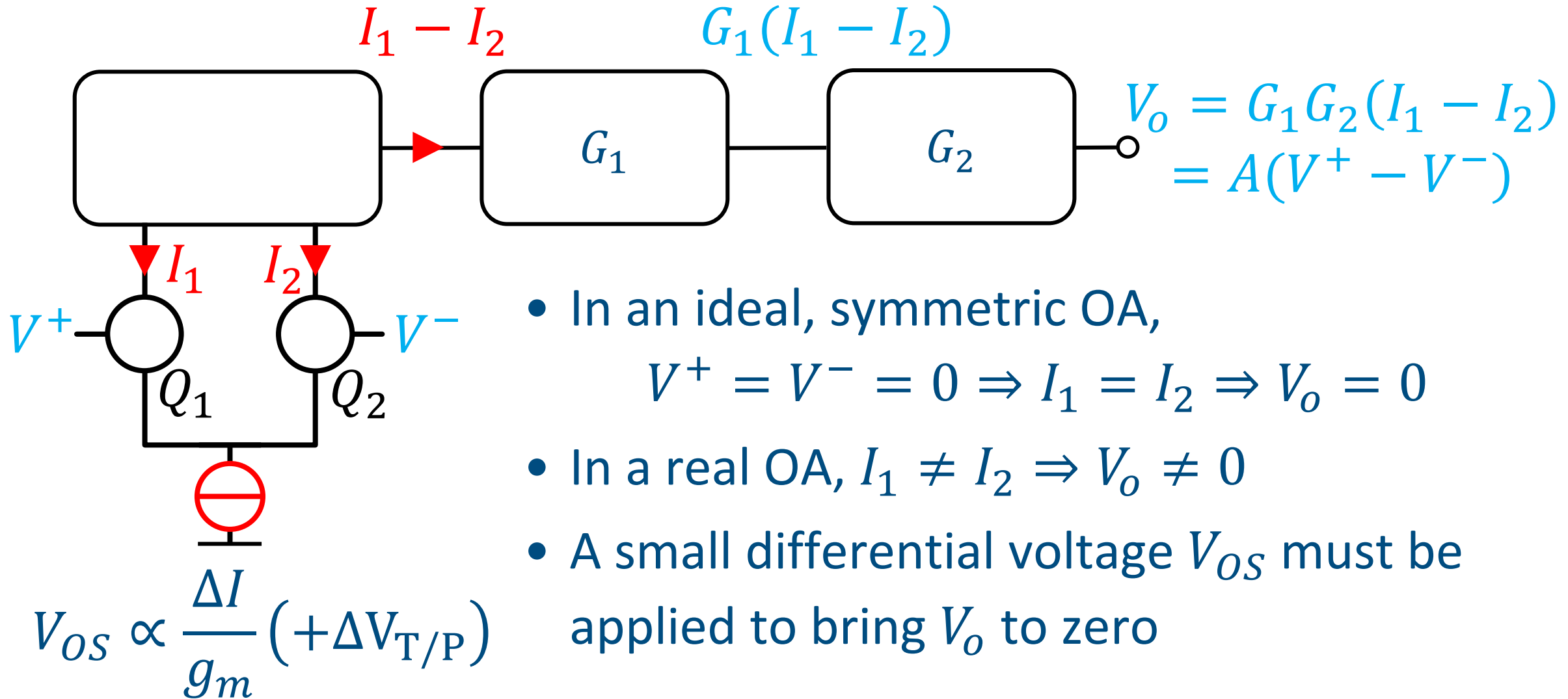


- In an ideal OA, $V_d = 0 \Rightarrow V_o = 0$
- In real OA, $V_d = 0 \Rightarrow V_o \neq 0$
- The offset voltage is the value of V_d that must be applied to bring the output to zero
- Typ. 1-5 mV (absolute value is always specified)
- **Precision OAs** have $V_{OS} < 1$ mV



Origin of offset voltage

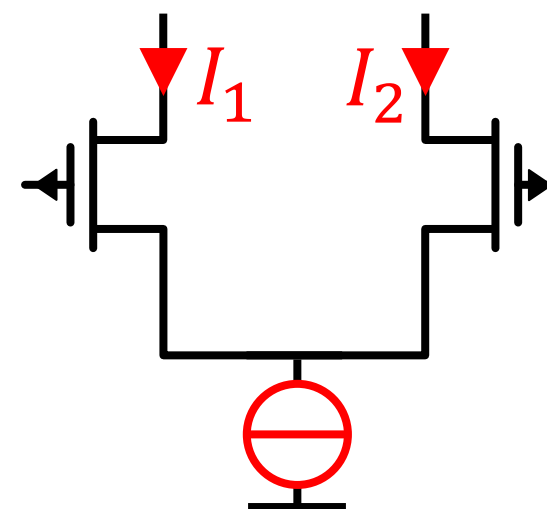
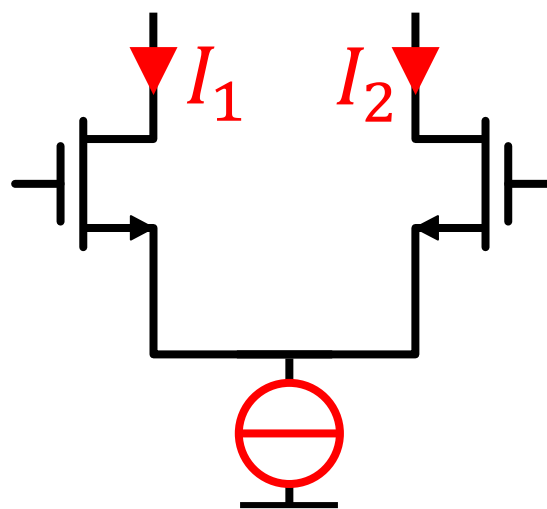
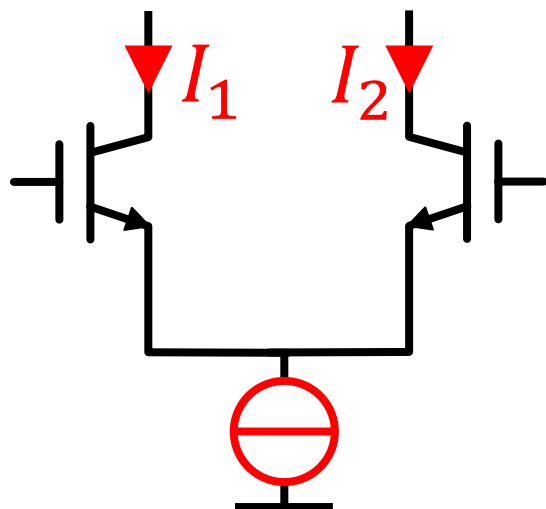
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Technology dependence

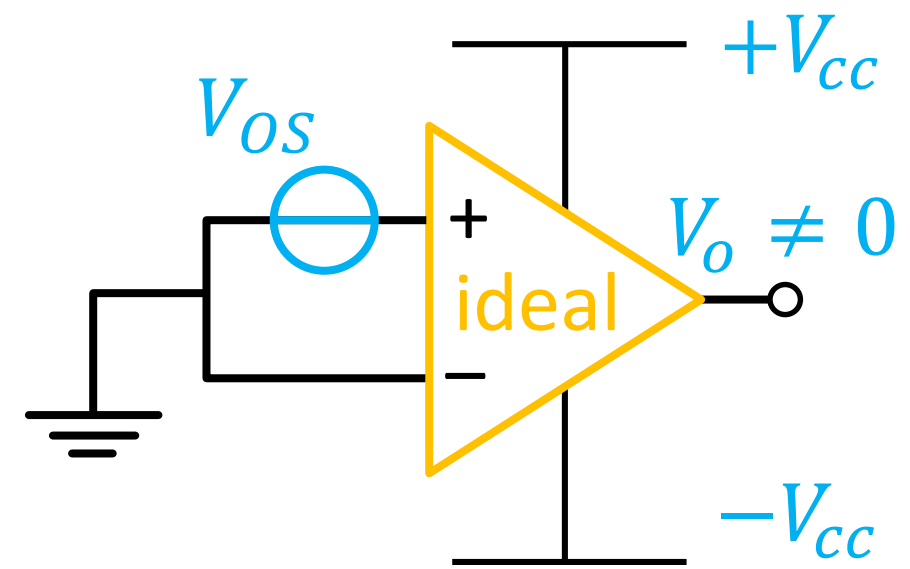
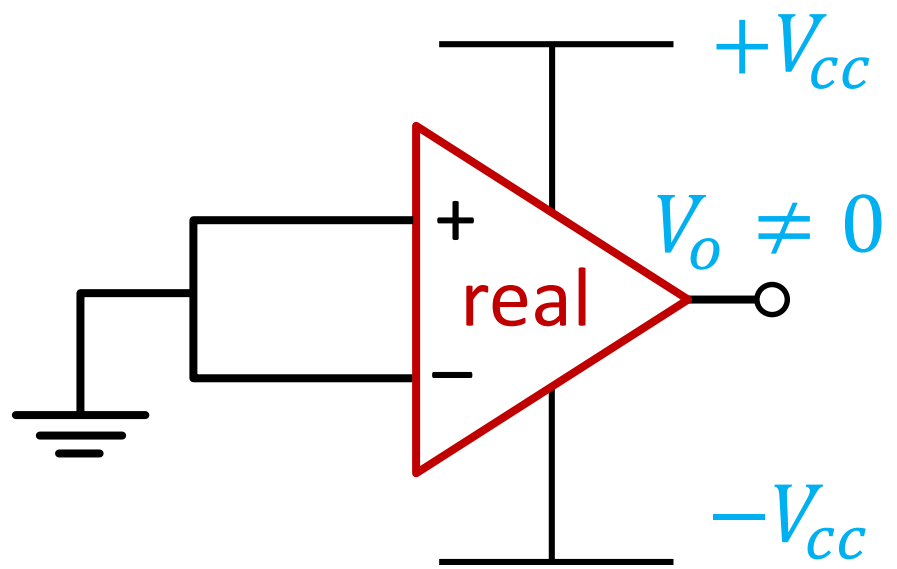
9



	BJT	MOS	JFET/BiFET
ΔI	small	large	large
g_m	large	small	small
$\Delta V_{T/P}$	0	fair	large
V_{OS}	small	fair	large



Offset voltage modeling and value



best

typ

BJT OAs

10 – 25 μV

150 μV – 10 mV

MOS OAs

< 100 μV – 1 mV

200 μV – 10 mV

JFET OAs

100 μV – 1 mV

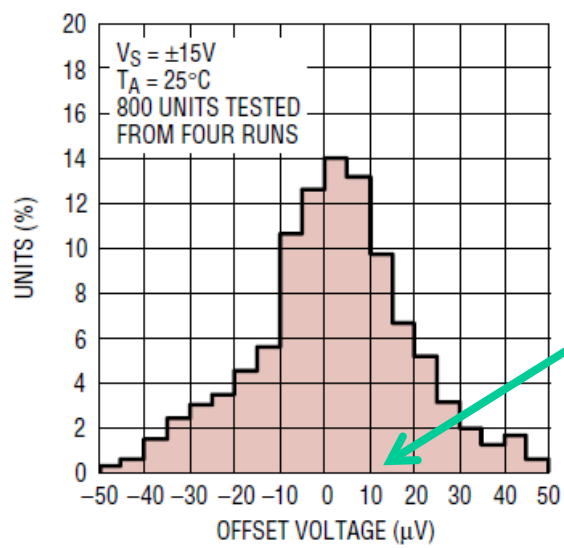
800 μV – 15 mV



- Describes the temperature dependence of V_{OS} (sometimes labelled as TCV_{OS})
- Typical values for general-purpose OAs are $1 - 10 \mu\text{V}/^\circ\text{C}$
- **Low-drift OAs** have $dV_{OS}/dT < 0.3 \mu\text{V}/^\circ\text{C}$
- «Chopper-stabilized» or «auto-zero» OA feature $V_{OS} < 1 \mu\text{V}$ and $dV_{OS}/dT < 30 \text{ nV}/^\circ\text{C}$ (more on this on the last lesson)

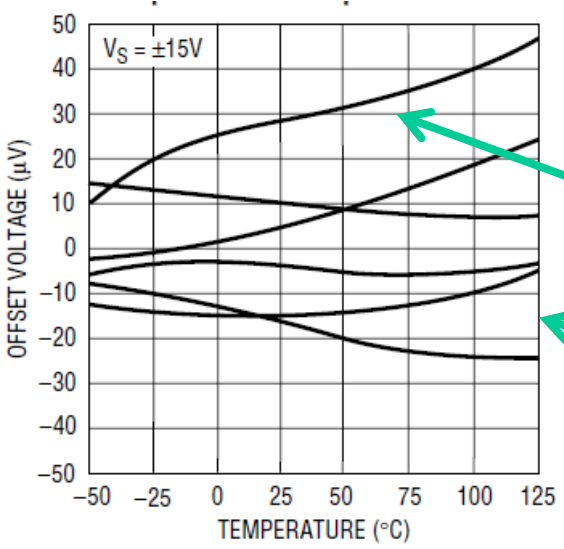


Actual values from datasheets



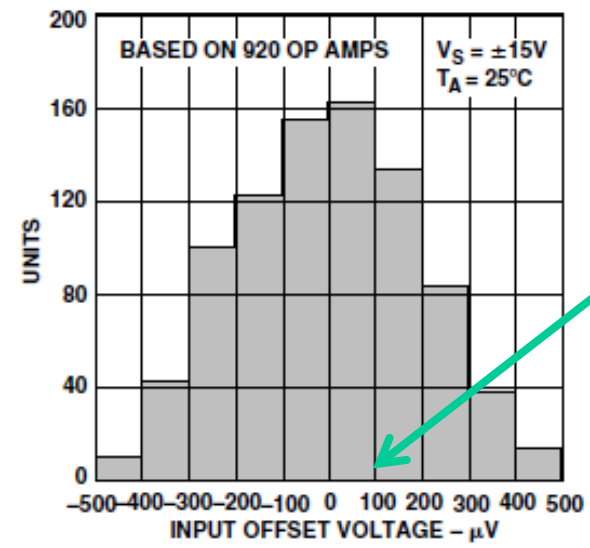
Scale=10 μV/div

BJT,
precision



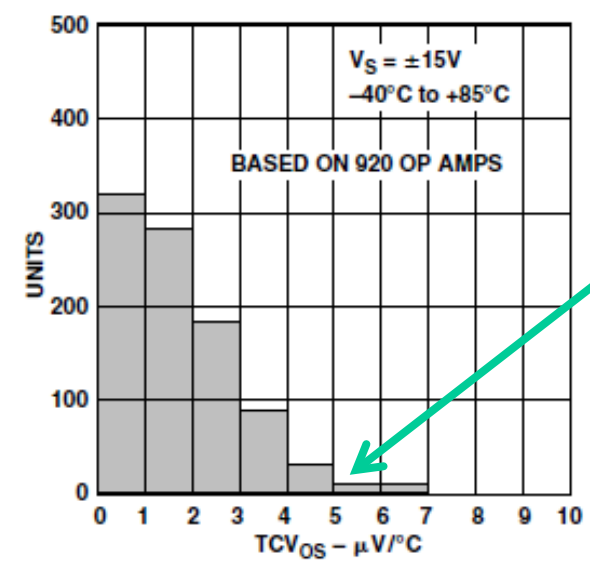
40 μV over 175°C
⇒ 0.23 μV/°C

Each device is
different!



Scale=100 μV/div

JFET

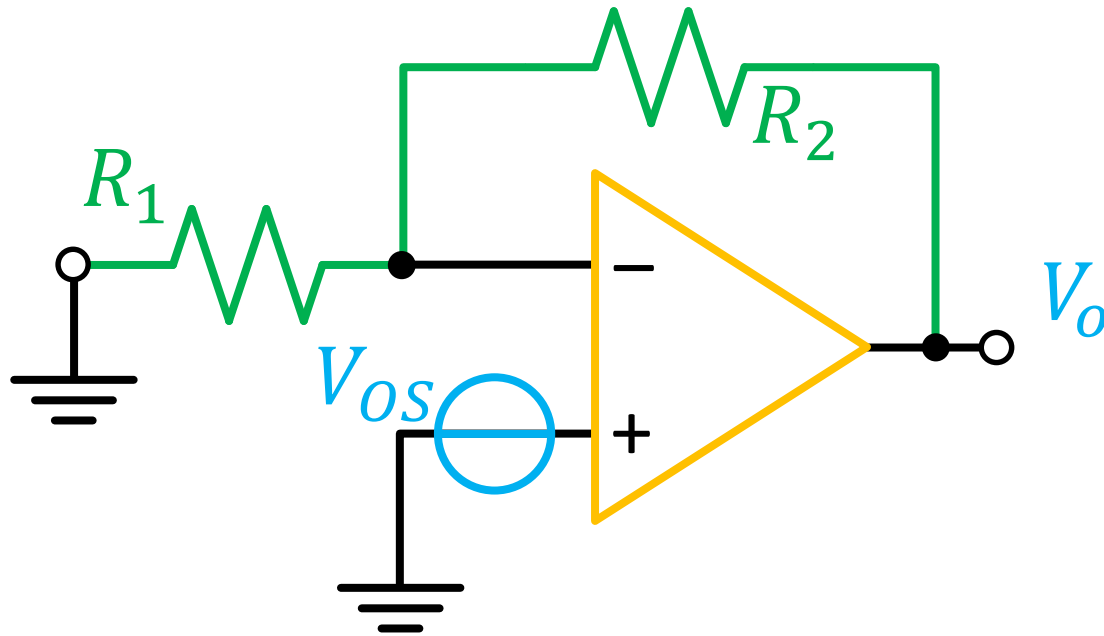


A few μV/°C



Output voltage

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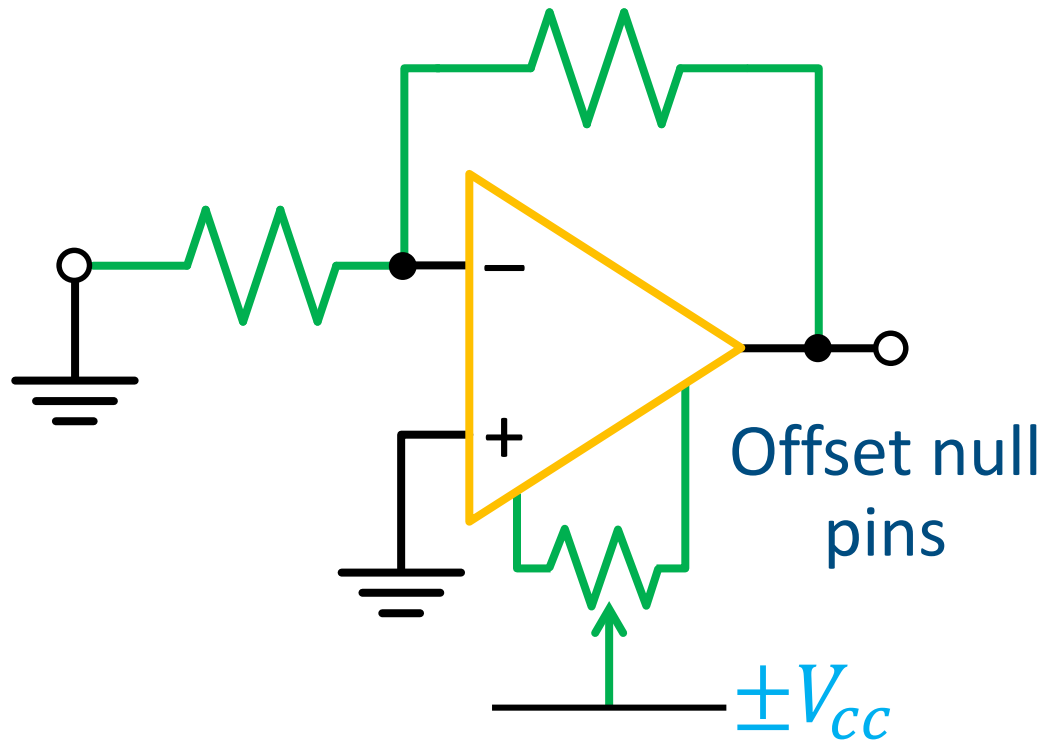
$$V_o = V_{os} \frac{R_1 + R_2}{R_1}$$

Same values for I and NI amplifiers



Offset compensation

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- Detailed compensation scheme provided by manufacturer
- Other schemes may be devised, i.e., biasing V^+ to get $V_o = 0$
- Obviously, drift or long-term stability cannot be compensated this way!

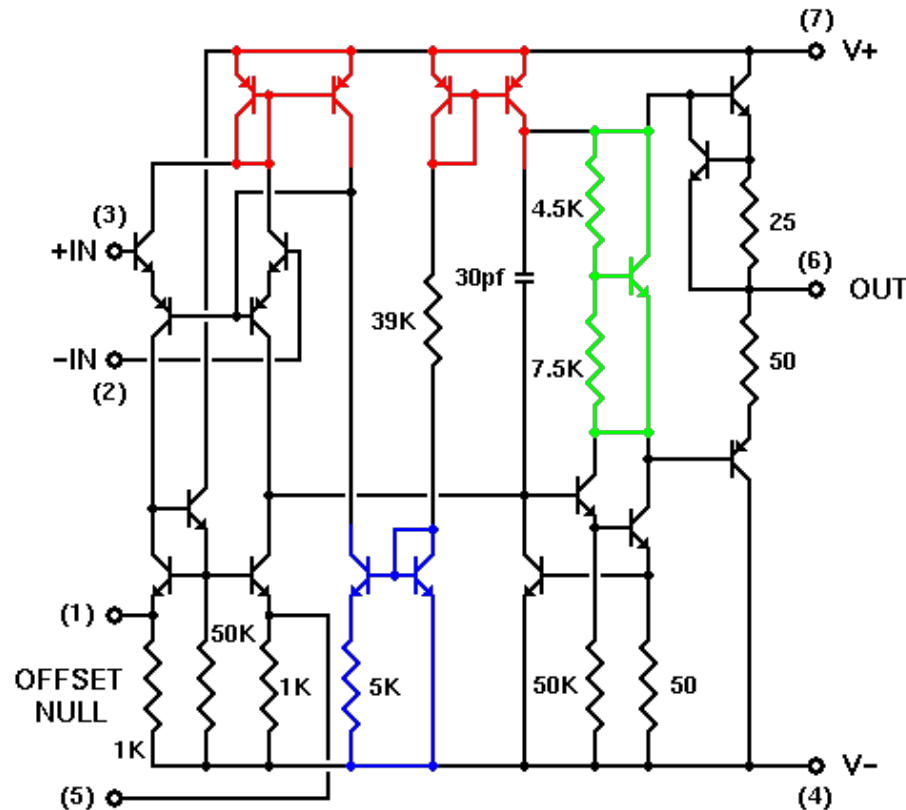


- Offset voltage
- Bias currents
- Effect on linear circuits



Input bias current

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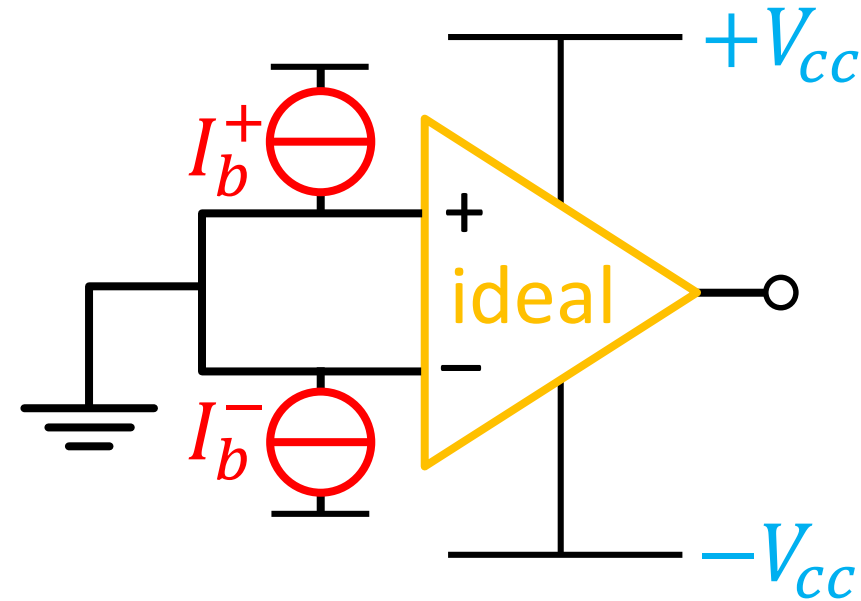
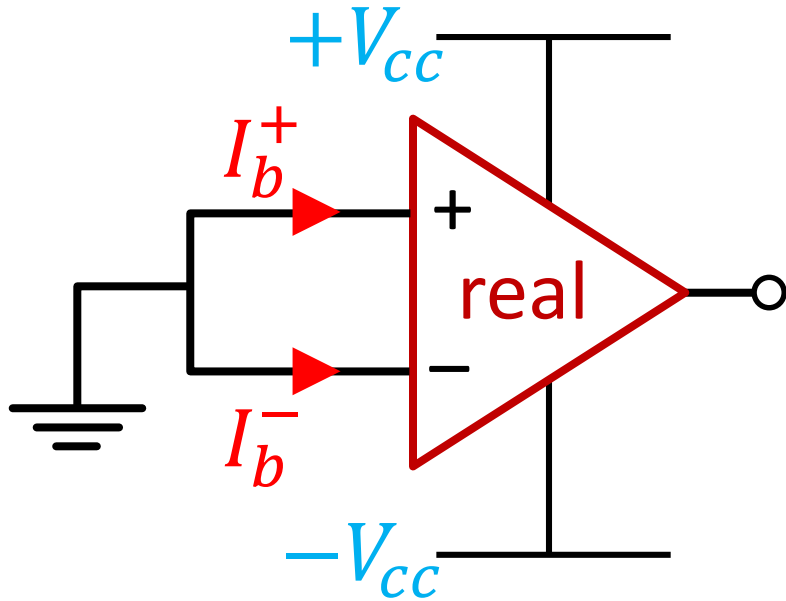


- BJTs in input stage require a DC base current I_b
- JFETs as input devices have reverse-biased $p-n$ junctions
- MOSFETs have ESD protection circuits (diodes) which determine I_b



Bias current modeling

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- Typ. BJT OA: $10^{-8} - 10^{-6}$ A
- Typ. JFET OA: $10^{-13} - 10^{-10}$ A
- Typ. CMOS OA: $10^{-13} - 10^{-10}$ A (ESD circ.)



- Bias currents at the two inputs are actually different, I_b^+ and I_b^-
- I_b is defined as their *average* value

$$I_B = \frac{I_b^+ + I_b^-}{2}$$

- Offset current is defined as $I_{OS} = |I_b^+ - I_b^-|$
- Usually, an order of magnitude smaller than I_b

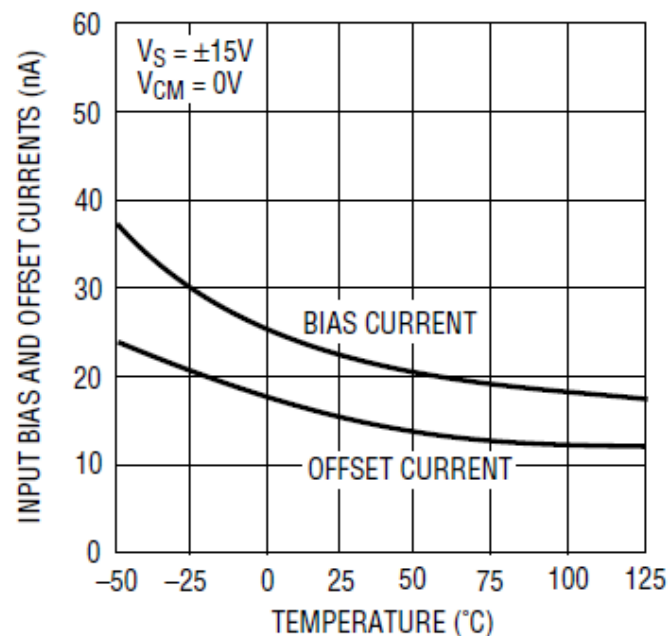


- In FET and CMOS OAs, I_b and I_{OS} increase by a factor of two every 10°C (reverse currents of p - n junctions) $\Rightarrow$ check T range if low current is needed!
- BJT OAs usually have lower drifts ($10 - 100 \text{ pA}/^\circ\text{C}$)

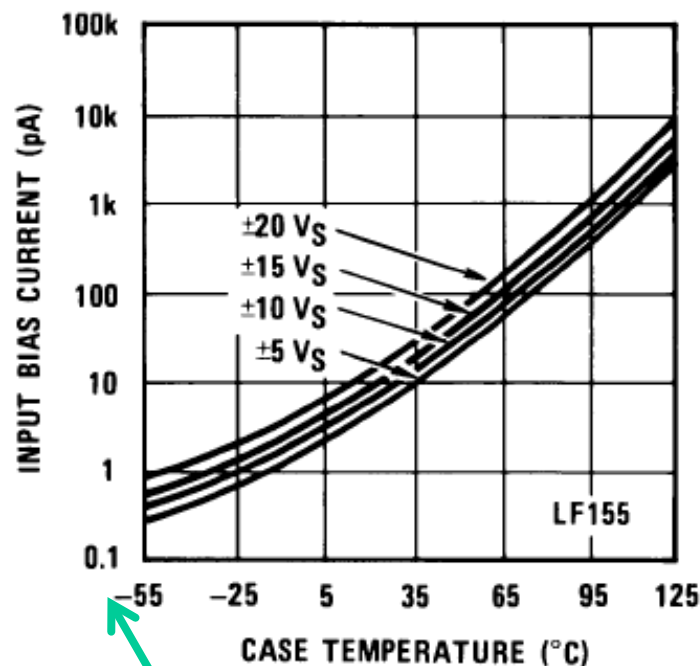


Actual values from datasheets

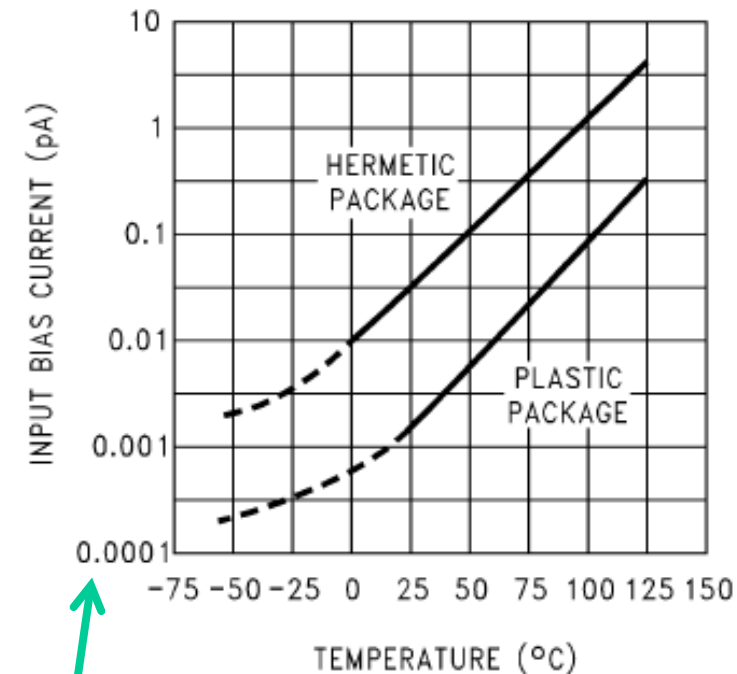
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BJT



JFET



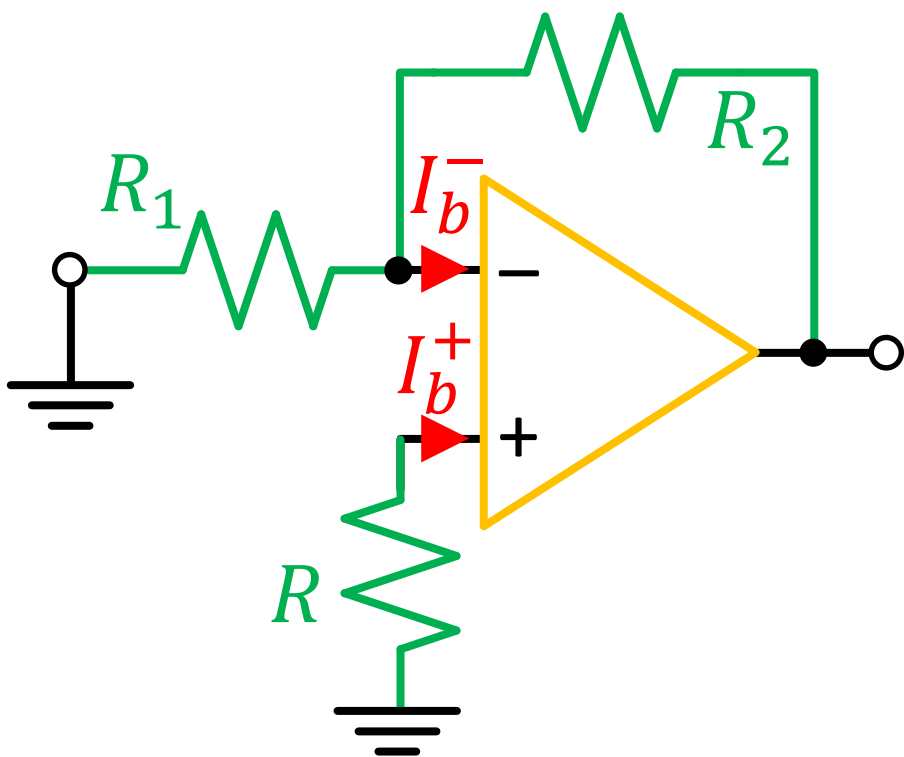
CMOS

Log scales $\Rightarrow$ Exponential dependence!



Bias current compensation

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$$\begin{aligned} V_o &= I_b^- R_2 - I_b^+ R \left(\frac{R_1 + R_2}{R_1} \right) \\ &= I_b R_2 \left(1 - \frac{R}{R_1 \parallel R_2} \right) \\ &\quad + I_{OS} \frac{R_2}{2} \left(1 + \frac{R}{R_1 \parallel R_2} \right) \end{aligned}$$

If $R = R_1 \parallel R_2$, I_b is compensated and $V_o = I_{OS} R_2$
(only useful if $I_{OS} \ll I_b$)

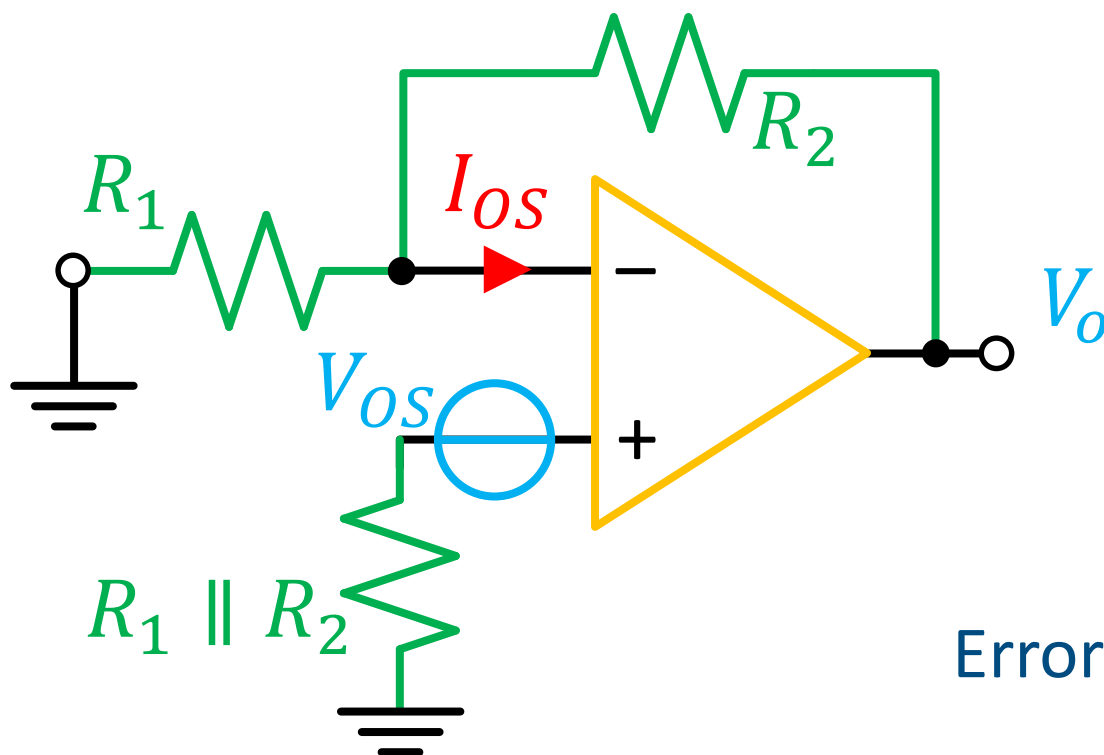


- Offset voltage
- Bias currents
- Effect on linear circuits



Total error – inverting amplifier

23



If I_b is compensated, symmetry allows to place just one I_{OS} source

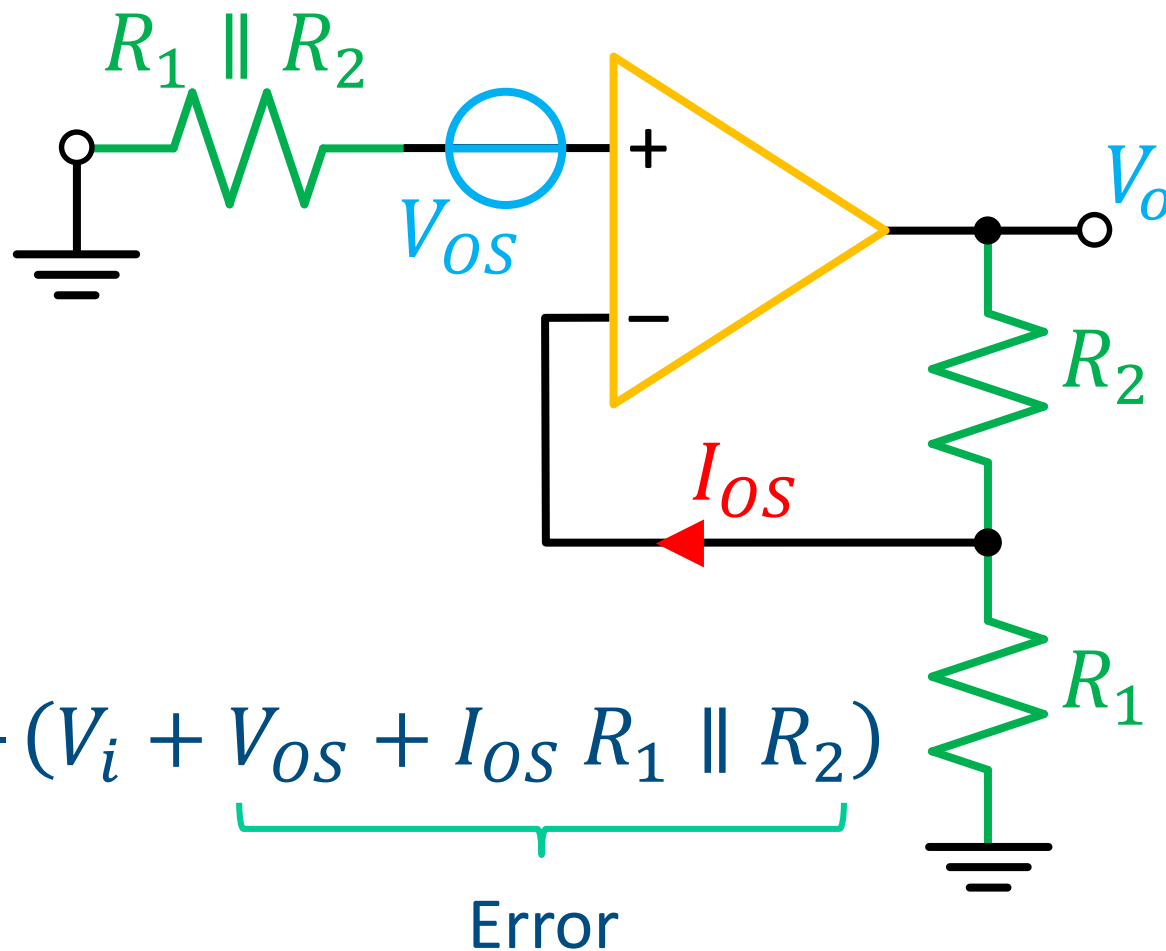
Error (trade-off with $R_{in} = R_1$)

$$V_o = -\frac{R_2}{R_1} \left(V_i + V_{OS} \frac{R_1 + R_2}{R_2} + I_{OS} R_1 \right)$$



Total error – non-inverting amplifier

24



$$V_o = \frac{R_1 + R_2}{R_1} (V_i + \underbrace{V_{OS} + I_{OS} R_1 \parallel R_2}_{\text{Error}})$$